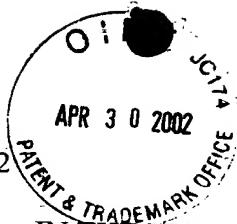


206569US2



IN THE UNITED STATES PATENT & TRADEMARK OFFICE

#8/A
5/2/02
Anne Th

IN RE APPLICATION OF :

Koichi MOTOIKE : EXAMINER: K. WELLS

SERIAL NO: 09/841,595 :

FILED: April 25, 2001 : GROUP ART UNIT: 2816

FOR: SEMICONDUCTOR
INTEGRATED CIRCUIT

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AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Responsive to the Official Action dated January 30, 2002, please amend the above-identified patent application as follows:

IN THE TITLE

Please replace the Title of the Invention with the following.

--SEMICONDUCTOR INTEGRATED CIRCUIT HAVING FET--.

IN THE CLAIMS

Please amend Claims 2-6, 12 and 13 as shown below in clean form. A marked-up copy of the amended claims is attached.

2. (Amended) A semiconductor integrated circuit as set forth in claim 1, which further comprises a first capacitor element provided between the gate terminal and the source terminal of said FET,

wherein a capacitance value of said first capacitor element is set so that a parasitic resistance component of said FET decreases when the drain voltage of said FET is lower than